

# DTC044T series

#### NPN 100mA 50V Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Value		
$V_{CEO}$	50V		
I <sub>C</sub>	60mA		
$R_1$	47kΩ		

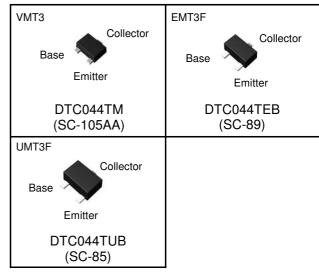
#### Features

- 1) Built-In Biasing Resistors
- 2) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 4) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Complementary PNP Types :DTA044T series
- 6) Lead Free/RoHS Compliant.

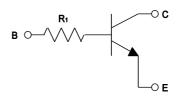
#### Application

Switching circuit, Inverter circuit, Interface circuit, Driver circuit

#### Outline



#### •Inner circuit



#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
DTC044TM	VMT3	1212	T2L	180	8	8,000	11
DTC044TEB	EMT3F	1616	TL	180	8	3,000	11
DTC044TUB	UMT3F	2021	TL	180	8	3,000	11

## ● **Absolute maximum ratings** (Ta = 25 °C)

Paramete	er	Symbol	Values	Unit
Collector-base voltage		V <sub>CBO</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V	
Emitter-base voltage	$V_{EBO}$	5	V	
Collector current	I <sub>C</sub>	60	mA	
Collector Power dissipation	DTC044TM DTC044TEB	P <sub>C</sub> *2	150	mW
	DTC044TUB	1	200	mW
Junction temperature	T <sub>j</sub>	150	∞	
Range of storage temperature		T <sub>stg</sub>	-55 to +150	∞

## •Electrical characteristics( $Ta = 25 \, ^{\circ}C$ )

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	$BV_CBO$	I <sub>C</sub> = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 50μA	5	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V	-	-	0.5	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	-	-	0.5	μΑ
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C / I_B = 5mA / 0.5mA$	-	0.05	0.15	V
DC current gain	h <sub>FE</sub>	$V_{CE}$ = 10V , $I_{C}$ = 5mA	100	-	600	-
Input resistance	R <sub>1</sub>	-	32.9	47	61.1	kΩ
Transition frequency	f <sub>T</sub> *1	$V_{CE} = 10V, I_{E} = -5mA,$ f = 100MHz	-	250	-	MHz

<sup>\*1</sup> Characteristics of built-in transistor

<sup>\*2</sup> Each terminal mounted on a reference footprint

#### ●Electrical characteristic curves(Ta = 25 °C)

Fig.2 Grounded emitter output characteristics 50 Ta=25ºC COLLECTOR CURRENT : I<sub>C</sub> (mA)  $I_B =$ 40 200μΑ 180µA 160µA 30 140µA 120µA 100µA 20 Αμ08 60μΑ 10 40µA 20µA 0A 0 0 5 10 **COLLECTOR TO EMITTER** VOLTAGE: V<sub>CF</sub> (V)

Fig.4 Collector-emitter saturation voltage

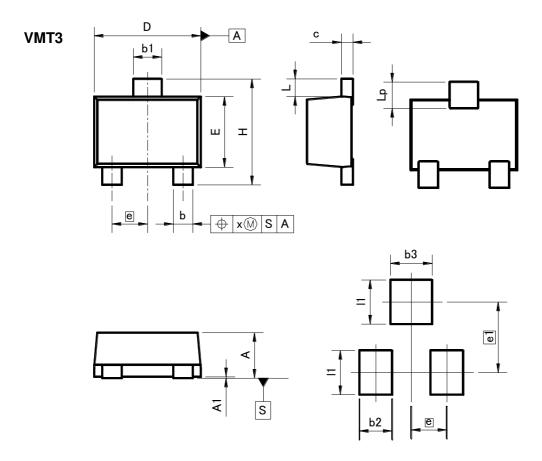
Fig.3 DC Current gain vs. Collector Current  $V_{CE}=10.0V$ Ta= $125^{\circ}C$ Ta= $75^{\circ}C$ Ta= $-40^{\circ}C$ 

VS. Collector Current

1

Ta=125°C
Ta=75°C
Ta=25°C
Ta=

## ●Dimensions (Unit:mm)



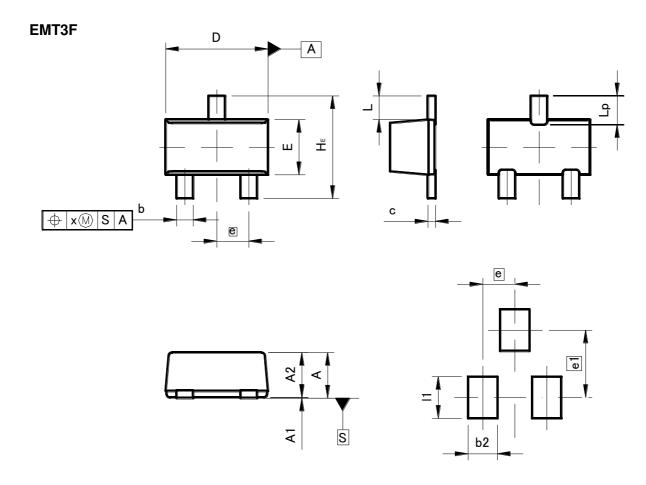
#### **Patterm of terminal position areas**

DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	0.45	0.55	0.018	0.022
A1	0.00	0.10	0	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
С	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
Е	0.70	0.90	0.028	0.035
е	0.4	40	0.0	02
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	_
Lp	0.20	0.40	0.008	_
х	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	0.8	80	0.03		
b2	_	0.37	-	0.015	
b3	_	0.47	ı	0.019	
11	_	0.50	_	0.02	

Dimension in mm/inches

## ●Dimensions (Unit:mm)



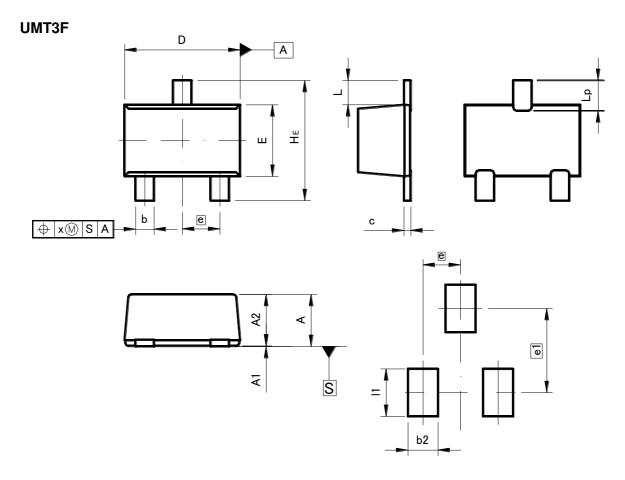
Patterm of terminal position areas

DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	0.65	0.85		
A1	0.00	0.10	0	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
Е	0.76	0.96	0.03	0.038
е	0.9	50	0.0	02
HE	1.50	1.70	0.059	0.067
L	0.3	37	0.0	15
Lp	0.35	0.55	0.014	0.022
Х	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
	DIM MIN		MAX	MIN	MAX
	e1	-	1.05	ı	0.041
Г	b2	-	0.46	-	0.018
	11	-	0.65	-	0.026

Dimension in mm/inches

## ●Dimensions (Unit:mm)



### Patterm of terminal position areas

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.85	1.05	0.033	0.041
A1	0.00	0.10	0	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
С	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
Е	1.15	1.35	0.045	0.053
е	0.0	65	0.0	03
HE	2.00	2.20	0.079	0.087
L	0.4	25	0.0	02
Lp	0.43	0.63	0.017	0.025
х	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIM MIN		MAX	MIN	MAX	
e1	1.4	47	0.058		
b2	_	0.52	-	0.02	
11	_	0.83	_	0.033	

Dimension in mm/inches

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